

Slawomir Kret

List of Publications by Year in descending order

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143
papers

1,944
citations

304368

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315357

38
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148
all docs

148
docs citations

148
times ranked

2397
citing authors

#	ARTICLE	IF	CITATIONS
1	Precise strain mapping of nano-twinned axial ZnTe/CdTe hetero-nanowires by scanning nanobeam electron diffraction. <i>Nanotechnology</i> , 2022, 33, 195704.	1.3	1
2	Bi incorporation and segregation in the MBE-grown GaAs-(Ga,Al)As-Ga(As,Bi) core-shell nanowires. <i>Scientific Reports</i> , 2022, 12, 6007.	1.6	1
3	Role of Metal Vacancies in the Mechanism of Thermal Degradation of InGaN Quantum Wells. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 7476-7484.	4.0	15
4	Structural defects in MBE-grown CdTe-basing heterojunctions designed for photovoltaic applications. <i>Semiconductor Science and Technology</i> , 2021, 36, 045022.	1.0	3
5	Phase-transition critical thickness of rocksalt Mg _x Zn _{1-x} O layers. <i>Journal of Chemical Physics</i> , 2021, 154, 154701.	1.2	4
6	Molecular Beam Epitaxy of a 2D Material Nearly Lattice Matched to a 3D Substrate: NiTe ₂ on GaAs. <i>Crystal Growth and Design</i> , 2021, 21, 5773-5779.	1.4	8
7	Near-infrared emission from spatially indirect excitons in type II ZnTe/CdSe/(Zn,Mg)Te core/double-shell nanowires. <i>Nanotechnology</i> , 2021, 32, 495202.	1.3	1
8	Oxidation of MBE-Grown ZnTe and ZnTe/Zn Nanowires and Their Structural Properties. <i>Materials</i> , 2021, 14, 5252.	1.3	2
9	Influence of Growth Polarity Switching on the Optical and Electrical Properties of GaN/AlGaIn Nanowire LEDs. <i>Electronics (Switzerland)</i> , 2021, 10, 45.	1.8	3
10	Charge transport in MBE-grown 2H-MoTe ₂ bilayers with enhanced stability provided by an AlO _x capping layer. <i>Nanoscale</i> , 2020, 12, 16535-16542.	2.8	8
11	Room temperature infrared detectors made of PbTe/CdTe multilayer composite. <i>Applied Physics Letters</i> , 2020, 117, 072102.	1.5	10
12	Polarization and magneto-optical properties of excitonic emission from wurtzite CdTe/(Cd,Mg)Te core/shell nanowires. <i>Nanotechnology</i> , 2020, 31, 215710.	1.3	4
13	Narrow Excitonic Lines and Large-Scale Homogeneity of Transition-Metal Dichalcogenide Monolayers Grown by Molecular Beam Epitaxy on Hexagonal Boron Nitride. <i>Nano Letters</i> , 2020, 20, 3058-3066.	4.5	35
14	Role of high nitrogen flux in InAlN growth by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2020, 544, 125720.	0.7	2
15	Experimental search for the origin of low-energy modes in topological materials. <i>Physical Review B</i> , 2019, 100, .	1.1	12
16	The critical role of N-vacancy on chemical composition fluctuations and degradation of InAlN layer. <i>Journal of Applied Physics</i> , 2019, 125, 215707.	1.1	5
17	Magneto-transport in inverted HgTe quantum wells. <i>Npj Quantum Materials</i> , 2019, 4, .	1.8	16
18	Enhanced Ferromagnetism in Cylindrically Confined MnAs Nanocrystals Embedded in Wurtzite GaAs Nanowire Shells. <i>Nano Letters</i> , 2019, 19, 7324-7333.	4.5	14

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19	Growth and optical properties of ZnO/Zn _{1-x} Mg _x O quantum wells on ZnO microrods. <i>Nanoscale</i> , 2019, 11, 2275-2281.	2.8	8
20	Evidence of relationship between strain and In-incorporation: Growth of N-polar In-rich InAlN buffer layer by OMCVD. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	10
21	Magnetic field induced mixing of light hole excitonic states in (Cd, Mn)Te/(Cd, Mg)Te core/shell nanowires. <i>Nanotechnology</i> , 2018, 29, 205205.	1.3	6
22	Compositional and strain analysis of In(Ga)N/GaN short period superlattices. <i>Journal of Applied Physics</i> , 2018, 123, 024304.	1.1	11
23	Self-organization process in crystalline PbTe/CdTe multilayer structures: Experiment and Monte Carlo simulations. <i>Journal of Alloys and Compounds</i> , 2018, 747, 809-814.	2.8	9
24	Defect-free SnTe topological crystalline insulator nanowires grown by molecular beam epitaxy on graphene. <i>Nanoscale</i> , 2018, 10, 20772-20778.	2.8	9
25	Influence of substrate temperature on incorporation of magnesium into Zn _{1-x} Mg _x O layers growth by molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2018, 766, 398-401.	2.8	3
26	Indium rich clusters in MOCVD InGaN/GaN: high resolution electron microscopy study and finite element modelling. , 2018, , 61-64.		0
27	Growth and optical investigations of high quality individual CdTe/(Cd,Mg)Te core/shell nanowires. <i>Nanotechnology</i> , 2017, 28, 045207.	1.3	6
28	Wurtzite (Ga,Mn)As nanowire shells with ferromagnetic properties. <i>Nanoscale</i> , 2017, 9, 2129-2137.	2.8	15
29	In Situ Electron Beam Amorphization of Sb ₂ Te ₃ within Single Walled Carbon Nanotubes. <i>Acta Physica Polonica A</i> , 2017, 131, 1324-1328.	0.2	1
30	FIB Method of Sectioning of III-V Core-Multi-Shell Nanowires for Analysis of Core/Shell Interfaces by High Resolution TEM. <i>Acta Physica Polonica A</i> , 2017, 131, 1332-1336.	0.2	2
31	Application of Graphics Processing Unit for In-Line Electron Holography. <i>Acta Physica Polonica A</i> , 2017, 131, 1353-1357.	0.2	1
32	TEM Study of the Structural Properties of Nanowires Based on Cd, Zn, Te grown by MBE on Silicon Substrates. <i>Acta Physica Polonica A</i> , 2017, 131, 1399-1405.	0.2	4
33	Off-Axis Electron Holography of Magnetic Nanostructures: Magnetic Behavior of Mn Rich Nanoprecipitates in (Mn,Ga)As System. <i>Acta Physica Polonica A</i> , 2017, 131, 1406-1409.	0.2	2
34	Synthesis and magneto-optic characterization of Cu-doped ZnO/MgO and ZnO/oleic acid core/shell nanoparticles. <i>RSC Advances</i> , 2016, 6, 44820-44825.	1.7	7
35	Coexistence of optically active radial and axial CdTe insertions in single ZnTe nanowire. <i>Nanoscale</i> , 2016, 8, 5720-5727.	2.8	7
36	Fine-Scale Skeletal Banding Can Distinguish Symbiotic from Asymbiotic Species among Modern and Fossil Scleractinian Corals. <i>PLoS ONE</i> , 2016, 11, e0147066.	1.1	25

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37	Extended defects in MBE-grown CdTe-based solar cells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 1115-1118.	0.8	2
38	Nanoscale morphology of multilayer PbTe/CdTe heterostructures and its effect on photoluminescence properties. <i>Nanotechnology</i> , 2015, 26, 135601.	1.3	9
39	Engineering the hole confinement for CdTe-based quantum dot molecules. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	2
40	Strain-induced energy gap variation in ZnTe/ZnMgTe core/shell nanowires. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	13
41	Enhanced catalyst-free nucleation of GaN nanowires on amorphous Al ₂ O ₃ by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2014, 115, 043517.	1.1	27
42	Laser-deposited Cu/Al ₂ O ₃ nanocomposite: experiment and modeling. <i>Applied Physics A: Materials Science and Processing</i> , 2014, 117, 169-173.	1.1	3
43	Strong s-d exchange coupling in ZnMnTe/ZnMgTe core/shell nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1308-1311.	0.8	1
44	All-Wurtzite (In,Ga)As-(Ga,Mn)As Core-Shell Nanowires Grown by Molecular Beam Epitaxy. <i>Nano Letters</i> , 2014, 14, 4263-4272.	4.5	29
45	Influence of hydrogen and TMI _n on indium incorporation in MOVPE growth of InGa _n layers. <i>Journal of Crystal Growth</i> , 2014, 402, 330-336.	0.7	26
46	The source of the threading dislocation in GaSb/GaAs hetero-structures and their propagation mechanism. <i>Applied Physics Letters</i> , 2013, 102, 052102.	1.5	17
47	Structural characterization of the epitaxially grown core-shell ZnTe/ZnMgTe nanowires. <i>Radiation Physics and Chemistry</i> , 2013, 93, 111-116.	1.4	0
48	Growth mechanisms in semipolar InN nanowires. http://www.w3.org/1998/Math/MathML altimg="si0020.gif" overflow="scroll" <mml:mo stretchy="false">(</mml:mo> <mml:mn>2</mml:mn> <mml:mspace width=".5em") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 307 Td (/ </mml:mo> </mml:math>	0.7	20
49	Influence of substrate nitridation temperature on epitaxial alignment of GaN nanowires to Si(111) substrate. <i>Nanotechnology</i> , 2013, 24, 035703.	1.3	74
50	Growth mode transition and relaxation of thin InGa _n layers on GaN (0001). <i>Journal of Crystal Growth</i> , 2013, 372, 65-72.	0.7	19
51	Antimony-Mediated Control of Misfit Dislocations and Strain at the Highly Lattice Mismatched GaSb/GaAs Interface. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 9760-9764.	4.0	9
52	Activation of an intense near band edge emission from ZnTe/ZnMgTe core/shell nanowires grown on silicon. <i>Nanotechnology</i> , 2013, 24, 365201.	1.3	13
53	Growth and characterizations of semipolar (112̂ ⁻²) InN. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	26
54	Thermal annealing of molecular beam epitaxy-grown InGa _n /GaN single quantum well. <i>Semiconductor Science and Technology</i> , 2012, 27, 105023.	1.0	14

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55	Mechanism of formation of the misfit dislocations at the cubic materials interfaces. Applied Physics Letters, 2012, 100, .	1.5	21
56	Low loss EEL spectroscopy performed on In _x Al _{1-x} N layers grown by MOVPE: comparison between experiment and ab-initio calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 989-992.	0.8	2
57	Giant Spin Splitting in Optically Active ZnMnTe/ZnMgTe Core/Shell Nanowires. Nano Letters, 2012, 12, 3404-3409.	4.5	32
58	Capture kinetics at deep-level defects in MBE-grown CdTe layers. Semiconductor Science and Technology, 2011, 26, 045008.	1.0	5
59	Magnetic properties of MnSb inclusions formed in GaSb matrix directly during molecular beam epitaxial growth. Journal of Applied Physics, 2011, 109, 074308.	1.1	14
60	Investigation of the anisotropic strain relaxation in GaSb islands on GaP. Journal of Applied Physics, 2011, 110, 043509.	1.1	10
61	Effects of the annealing temperature on the structural and electronic properties of MBE grown InGaN/GaN quantum wells. Journal of Physics: Conference Series, 2011, 326, 012012.	0.3	1
62	TEM and XANES study of MOVPE grown InAlN layers with different indium content. Journal of Physics: Conference Series, 2011, 326, 012013.	0.3	10
63	Surface morphology created by nanosecond laser annealing of amorphised Si layer – Investigations by complementary methods. Radiation Physics and Chemistry, 2011, 80, 1031-1035.	1.4	1
64	Investigation of the In composition in InGaN/GaN quantum wells deposited by MOVPE and/or MBE with emission from violet to green. Physica Status Solidi (B): Basic Research, 2011, 248, 1187-1190.	0.7	14
65	Structural and magnetic properties of GaSb:MnSb granular layers. Radiation Physics and Chemistry, 2011, 80, 1051-1057.	1.4	5
66	Growth and optical properties of CdTe quantum dots in ZnTe nanowires. Applied Physics Letters, 2011, 99, 113109.	1.5	14
67	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metal-Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	0.8	8
68	Morphology and Selected Properties of Core/Shell ZnTe-Based Nanowire Structures Containing ZnO. Acta Physica Polonica A, 2011, 119, 612-614.	0.2	3
69	Impact of Thin LT-GaN Cap Layers on the Structural and Compositional Quality of MOVPE Grown InGaN Quantum Wells Investigated by TEM. Acta Physica Polonica A, 2011, 119, 660-662.	0.2	1
70	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metal-Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	0.8	3
71	Inhomogeneities of InGaN/GaN MOVPE multi quantum wells grown with a two temperatures process studied by transmission electron microscopy. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1101-1104.	0.8	10
72	TEM investigation of a processed InGaN based laser grown by PAMBE on bulk GaN substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1325-1328.	0.8	2

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73	TEM characterization of MBE grown CdTe/ZnTe axial nanowires. Journal of Microscopy, 2010, 237, 337-340.	0.8	7
74	Zn _{1-x} Mn _x Te-based diluted magnetic semiconductor nanowire structures grown by MBE. , 2010, , .		2
75	CdTe Quantum Dots in a Field Effect Structure: Photoluminescence Lineshape Analysis. , 2010, , .		0
76	(Zn,Mn)Te-Based Nanowires for Spintronic Applications: A TEM Study of Structural and Chemical Properties. Materials Science Forum, 2010, 638-642, 2154-2159.	0.3	2
77	ZnTe“ZnO core“shell radial heterostructures grown by the combination of molecular beam epitaxy and atomic layer deposition. Nanotechnology, 2010, 21, 015302.	1.3	28
78	Structural and magnetic properties of the molecular beam epitaxy grown MnSb layers on GaAs substrates. Journal of Applied Physics, 2009, 106, .	1.1	9
79	TEM analysis of the container effect of Au-based catalyst droplets during vapour-liquid-solid growth of axial ZnTe/CdTe nanowires. Crystal Research and Technology, 2009, 44, 1047-1053.	0.6	5
80	Three-dimensional localization of excitons in the InAs/GaAs wetting layer “ magnetospectroscopic study. Physica Status Solidi (B): Basic Research, 2009, 246, 850-853.	0.7	3
81	TEM determination of directions of (Ga,Mn)As nanowires grown by MBE on GaAs(001) substrates. Journal of Microscopy, 2009, 236, 115-118.	0.8	6
82	Influence of the Si cap layer on the SiGe islands morphology. Micron, 2009, 40, 122-125.	1.1	9
83	Elaboration of (111) oriented 3C-SiC/Si layers for template application in nitride epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 9-14.	1.7	28
84	UV-excited piezo-optical effects in oxide nanocrystals incorporated into PMMA matrices. Acta Materialia, 2008, 56, 5677-5684.	3.8	22
85	Zn _{1-x} Mn _x Te Diluted Magnetic Semiconductor Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2008, 8, 4061-4065.	4.5	19
86	Atomic order in magnetic Mn inclusions in Si crystals: XAS and TEM studies. Journal of Non-Crystalline Solids, 2008, 354, 4189-4192.	1.5	1
87	TEM characterization of VLS-grown ZnTe nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3780-3784.	0.8	15
88	Observation of Asymmetric Wafer Bending for 3C-SiC Thin Films Grown on Misoriented Silicon Substrates. Materials Research Society Symposia Proceedings, 2008, 1069, 1.	0.1	5
89	Zn _{1-x} Mg _x Te nanowires grown by solid source molecular beam epitaxy. Nanotechnology, 2008, 19, 365606.	1.3	9
90	Natural quantum dots in the InAs-GaAs wetting layer. Applied Physics Letters, 2008, 92, 171104.	1.5	27

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91	Structural and Chemical Properties of ZnTe Nanowires Grown on GaAs. Springer Proceedings in Physics, 2008, , 233-236.	0.1	1
92	Neutral and Charged Excitons Localized in the InAs/GaAs Wetting Layer. Acta Physica Polonica A, 2008, 114, 1055-1060.	0.2	3
93	MBE Growth and Properties of ZnTe- and CdTe-Based Nanowires. Journal of the Korean Physical Society, 2008, 53, 3055-3063.	0.3	26
94	Analysis of atomic structure and structural imperfections of ZnTe and (Zn,Mn)Te nanowires. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C598-C598.	0.3	0
95	TEM analysis of the chemical gradient in (Zn,Mn)Te/ZnTe nanowires. , 2008, , 301-302.		0
96	The effect of local atomic structure on the optical properties of GeSi self-assembled islands buried in silicon matrix. Nanotechnology, 2007, 18, 115711.	1.3	13
97	A transmission electron microscopy study of composition in Si _{1-x} Gex/Si (001) quantum dots. Philosophical Magazine, 2007, 87, 1531-1543.	0.7	2
98	Structure of Magnetically Ordered Si:Mn. Solid State Phenomena, 2007, 131-133, 327-332.	0.3	1
99	Catalytic growth of ZnTe nanowires by molecular beam epitaxy: structural studies. Nanotechnology, 2007, 18, 475606.	1.3	55
100	Homogenous indium distribution in InGaN/GaN laser active structure grown by LP-MOCVD on bulk GaN crystal revealed by transmission electron microscopy and x-ray diffraction. Nanotechnology, 2007, 18, 465707.	1.3	23
101	GaAs:Mn Nanowires Grown by Molecular Beam Epitaxy of (Ga,Mn)As at MnAs Segregation Conditions. Nano Letters, 2007, 7, 2724-2728.	4.5	47
102	ZnSe/CdSe Superlattice Nanowires by Catalyst-assisted Molecular Beam Epitaxy. AIP Conference Proceedings, 2007, , .	0.3	3
103	The Peak Pairs algorithm for strain mapping from HRTEM images. Ultramicroscopy, 2007, 107, 1186-1193.	0.8	230
104	Growth and Properties of ZnMnTe Nanowires. Acta Physica Polonica A, 2007, 112, 351-356.	0.2	4
105	Photoluminescence Properties of ZnO and ZnCdO Nanowires. Acta Physica Polonica A, 2007, 112, 357-362.	0.2	5
106	ZnTe nanowires grown catalytically on GaAs (001) substrates by molecular beam epitaxy. AIP Conference Proceedings, 2007, , .	0.3	0
107	Quantitative Strain Mapping Applied to Aberration-Corrected HAADF Images. Microscopy and Microanalysis, 2006, 12, 285-294.	0.2	22
108	Strain, Chemical Composition, and Defects Analysis at Atomic Level in GaN-based Epitaxial Layers. , 2006, , 439-488.		0

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109	An approach to the systematic distortion correction in aberration-corrected HAADF images. Journal of Microscopy, 2006, 221, 1-7.	0.8	34
110	Piezoelectric field around threading dislocation in GaN determined on the basis of high-resolution transmission electron microscopy image. Journal of Microscopy, 2006, 223, 212-215.	0.8	5
111	ZnTe nanowires grown on GaAs(100) substrates by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 133114.	1.5	71
112	Size and shape of In rich clusters and InGaN QWs at the nanometer scale. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2381-2384.	0.8	0
113	Self-organized MnAs quantum dots formed during annealing of GaMnAs under arsenic capping. Applied Physics Letters, 2005, 87, 263114.	1.5	18
114	Quantitative evaluation of the atomic structure of defects and composition fluctuations at the nanometer scale inside InGaN/GaN heterostructures. Physica Status Solidi (B): Basic Research, 2004, 241, 2735-2738.	0.7	5
115	Nonlinear FE analysis of residual stresses induced by dislocations in heterostructures. Computational Materials Science, 2004, 29, 379-395.	1.4	25
116	Modelling of indium rich clusters in MOCVD In Ga _{1-x} N/GaN multilayers. Journal of Alloys and Compounds, 2004, 382, 10-16.	2.8	0
117	Contribution to quantitative measurement of the In composition in GaN/InGaN multilayers. Materials Chemistry and Physics, 2003, 81, 273-276.	2.0	2
118	Investigation of the InGaN Quantum Wells Compositional Inhomogeneity. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 307-310.	0.8	1
119	Evidence of strong indium segregation in MOCVD In _x Ga _{1-x} N/GaN quantum layers. Materials Research Society Symposia Proceedings, 2003, 798, 176.	0.1	0
120	On the measurement of dislocation core distributions in a GaAs/ZnTe/CdTe heterostructure by high-resolution transmission electron microscopy. Philosophical Magazine, 2003, 83, 231-244.	0.7	21
121	Composition fluctuation in InGaN quantum wells made from molecular beam or metalorganic vapor phase epitaxial layers. Journal of Applied Physics, 2002, 91, 8979-8985.	1.1	92
122	Finite Element Simulation of Residual Stresses in Epitaxial Layers. Materials Science Forum, 2002, 404-407, 141-146.	0.3	2
123	Nanometric Scale Investigation of Local Strain in GaInAs Islands by High Resolution and Analytical TEM. Microscopy and Microanalysis, 2002, 8, 312-318.	0.2	6
124	Indium distribution inside quantum wells: The effect of growth interruption in MBE. Materials Research Society Symposia Proceedings, 2002, 743, L6.6.1.	0.1	0
125	The dislocations of low-angle grain boundaries in GaN epilayers: a HRTEM quantitative study and finite element stress state calculation. Diamond and Related Materials, 2002, 11, 910-913.	1.8	10
126	Three-Dimensional Quantum Dot "Crystal" Formation in CdTe/ZnTe Superlattices. Physica Status Solidi (B): Basic Research, 2002, 229, 445-448.	0.7	1

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127	Quantitative measurement of In fluctuation inside MOCVD InGaN QWs. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 93, 185-188.	1.7	5
128	Nanostructure of Si-Ge Near-Surface Layers Produced by Ion Implantation and Laser Annealing. <i>Acta Physica Polonica A</i> , 2002, 102, 259-264.	0.2	4
129	Extracting Quantitative Information from High Resolution Electron Microscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 227, 247-295.	0.7	111
130	Structural and optical evidence of island correlation in CdTe/ZnTe superlattices. <i>Applied Physics Letters</i> , 2001, 78, 3884-3886.	1.5	42
131	Analysis of strain in sub-grains with variable misorientation in GaN epilayers by digital processing of HRTEM images. <i>Materials Research Society Symposia Proceedings</i> , 2000, 639, 11541.	0.1	1
132	Analysis of strain in the {112},0} prismatic fault in GaN using digital processing of high-resolution transmission electron microscopy images. <i>Journal of Physics Condensed Matter</i> , 2000, 12, 10249-10256.	0.7	10
133	Measurement of dislocation core distribution by digital processing of high-resolution transmission electron microscopy micrographs: a new technique for studying defects. <i>Journal of Physics Condensed Matter</i> , 2000, 12, 10313-10318.	0.7	19
134	Magneto-optical Properties of Graded Quantum Well Structures Made of Diluted Magnetic Semiconductors. , 2000, , 237-246.		1
135	Local Stress in Highly Strained Coherent InGaAs Islands. <i>Materials Science Forum</i> , 1999, 294-296, 649-652.	0.3	0
136	High resolution electron microscope analysis of lattice distortions and In segregation in highly strained In _{0.35} Ga _{0.65} As coherent islands grown on GaAs (001). <i>Journal of Applied Physics</i> , 1999, 86, 1988-1993.	1.1	51
137	Atomic-scale mapping of local lattice distortions in highly strained coherent islands of In _x Ga _{1-x} As/GaAs by high-resolution electron microscopy and image processing. <i>Philosophical Magazine Letters</i> , 1998, 77, 249-256.	0.5	21
138	Strain Relaxation of ZnTe/CdTe and CdTe/ZnTe heterostructures: In Situ Study. <i>Acta Physica Polonica A</i> , 1996, 90, 911-914.	0.2	5
139	Digital Magnetic Quantum Wells for the Study of Interface Sharpness of Molecular Beam Epitaxy Grown Structures. <i>Acta Physica Polonica A</i> , 1995, 87, 165-168.	0.2	6
140	Lattice Parameter Relaxation during MBE of ZnTe/Cd _{1-x} Zn _x Te/Cd _{0.5} Zn _{0.5} Te Buffer Layers by RHLED and HRTEM. <i>Acta Physica Polonica A</i> , 1995, 88, 795-798.	0.2	2
141	Role of Substrate Misorientation in Relaxation of 3C-SiC Layers on Silicon. <i>Materials Science Forum</i> , 0, 615-617, 169-172.	0.3	8
142	Chemical composition and strain distribution of InAs/GaAs(001) stacked quantum rings. , 0, , 271-274.		0
143	Quantitative measurements of the inhomogeneous strain field of stacked self-assembled InAs/InP(001) quantum wires by the Peak Finding Method. , 0, , 299-302.		1